

build up a semiconducting layer, wherein the substrate is periodically protected from the heating element and/or the gas, present in the vessel, by means of a displaceable isolating shutter, and wherein said resultant device has a substantially consistent gate voltage and has a saturation mobility in the range of about 0.001 to about 100 cm²/V.s.

33. A device obtainable according to the process of claim 32 wherein said device has a saturation mobility in the range of about 0.001 to about 10 cm²/V.s.

34. A device obtainable according to the process of claim 32 wherein said device has a saturation mobility in the range of about 0.1 to about 1.00 cm²/V.s.--

REMARKS

Entry of this preliminary amendment in the file of this application is respectfully requested.

By this amendment, claims 21 and 23 have been cancelled, without prejudice, to their subsequent prosecution in any continuing application or disclaimer of any of the proprietary rights set forth therein. Claims 22 and 24 have been amended. Claims 28-34 have been added. Claims 22, 24 and 28-34 remain pending in this application.

This preliminary amendment has been presented to clarify the pending claims and place the claims in a form which is more in accordance with U.S. practice.

No additional fee is believed to be required for the filing of this preliminary amendment, but if such is, please charge it for this application to Deposit Account No. 50-0320.

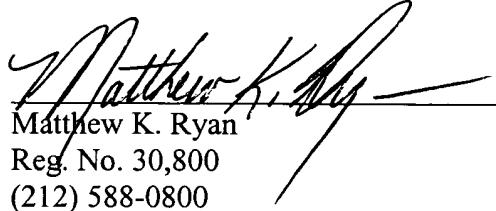
Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "Version with Markings to Show Changes Made."

Early consideration of this application on the merits is requested.

Respectfully submitted,

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VERSIONS WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

Claim 21 has been cancelled, without prejudice.

Claim 22 has been rewritten as follows:

--22. (Amended) An electronic device [Device, in particular being a transistor said device] having a substantially consistent gate voltage and a saturation mobility μ in the range of about 0.001 to about 100[, for example about 0.001 to about 10 and most preferably from about 0.1 to about 1.0] $\text{cm}^2/\text{V.s.}$ --

Claim 23 has been cancelled, without prejudice.

Claim 24 has been rewritten as follows:

--24. (Amended) A device [Device] comprising a substantially exclusive polycrystalline Si:H or a polycrystalline and amorphous Si:H layer, said device having a substantially consistent gate voltage and a saturation mobility lying in the range of about 0.001 to about 1000 [0.001-1000, for example 0.001 to 500] $\text{cm}^2/\text{V.s.}$ --

Claims 28-34 have been added as follows:

--28. The electronic device of claim 22 which has a saturation mobility in the range of about 0.001 to about 10 $\text{cm}^2/\text{V.s.}$

29. The electronic device of claim 22 which has a saturation mobility in the range of between about 0.1 to about 1.00 $\text{cm}^2/\text{V.s.}$

30. The electronic device of claim 22 which is a transistor.

31. The device comprising a substantially exclusive polycrystalline Si:H or a polycrystalline and amorphous Si:H layer of claim 24 wherein said device has a saturation mobility lying in the range of about 0.001 to about 500 $\text{cm}^2/\text{V.s.}$

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32. A device obtainable according to a process for providing a semiconducting device comprising the steps of depositing a semiconducting layer onto a substrate situated in a vessel by means of heating a gas to a predetermined, dissociation temperature so that the gas dissociates into fractions, whereby those fractions subsequently condense on the substrate to build up a semiconducting layer, wherein the substrate is periodically protected from the heating element and/or the gas, present in the vessel, by means of a displaceable isolating shutter, and wherein resultant device has a substantially consistent gate voltage and has a saturation mobility in the range of about 0.001 to about 100 cm²/V.s.

33. A device obtainable according to the process of claim 32 wherein said device has a saturation mobility in the range of about 0.001 to about 10 cm²/V.s.

34. A device obtainable according to the process of claim 32 wherein said device has a saturation mobility in the range of about 0.1 to about 1.00 cm²/V.s.--